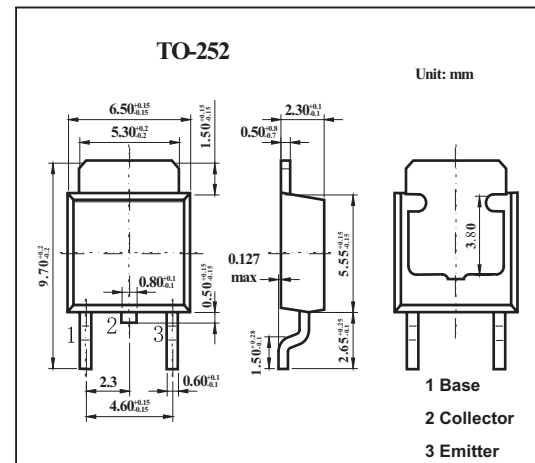


PNP Epitaxial Silicon Transistor

MJD350

■ Features

- Load Formed for Surface Mount Application
- Straight Lead

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-3	V
Collector Current (DC)	I_C	-0.5	A
Collector Current (Pulse)	I_{CP}	-0.75	A
Collector Dissipation ($T_C = 25^\circ\text{C}$)	P_C	15	A
Collector Dissipation ($T_a = 25^\circ\text{C}$)		1.56	W
Junction Temperature	T_J	150	W
Storage Temperature	T_{STG}	-65 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage *	$V_{CE0(sus)}$	$I_C = 1\text{mA}, I_E = 0$	-300			V
Collector Cut-off Current	I_{CEO}	$V_{CB} = -300\text{V}, I_E = 0$			-0.1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-0.1	mA
DC Current Gain *	h_{FE}	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$	30		240	

*Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$